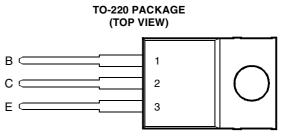
## BDX53, BDX53A, BDX53B, BDX53C NPN SILICON POWER DARLINGTONS

# BOURNS®

- Designed for Complementary Use with BDX54, BDX54A, BDX54B and BDX54C
- 60 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h<sub>FE</sub> of 750 at 3V, 3 A



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
	BDX53		45	
Collector-base voltage ( $I_E = 0$ )	BDX53A	V	60	v
	BDX53B	V <sub>CBO</sub>	80	v
	BDX53C		100	
	BDX53		45	
Callector emitter voltage (I 0)	BDX53A	V	60	V
Collector-emitter voltage ( $I_B = 0$ )	BDX53B	V <sub>CEO</sub>	80	
	BDX53C		100	
Emitter-base voltage	V <sub>EBO</sub>	5	V	
Continuous collector current	Ι <sub>C</sub>	8	A	
Continuous base current	I <sub>B</sub>	0.2	A	
Continuous device dissipation at (or below) 25°C case temperature (see No	P <sub>tot</sub>	60	W	
Continuous device dissipation at (or below) 25°C free air temperature (see N	P <sub>tot</sub>	2	W	
Operating junction temperature range	т <sub>і</sub>	-65 to +150	°C	
Operating temperature range	T <sub>stg</sub>	-65 to +150	°C	
Operating free-air temperature range	T <sub>A</sub>	-65 to +150	°C	

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

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## BDX53, BDX53A, BDX53B, BDX53C NPN SILICON POWER DARLINGTONS



#### electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TES	CONDITIONS		MIN	ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = 100 mA	I <sub>B</sub> = 0	(see Note 3)	BDX53 BDX53A BDX53B BDX53C	45 60 80 100			V
I <sub>CEO</sub>	Collector-emitter cut-off current	$V_{CE} = 30 V$ $V_{CE} = 30 V$ $V_{CE} = 40 V$ $V_{CE} = 50 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDX53 BDX53A BDX53B BDX53C			0.5 0.5 0.5 0.5	mA
I <sub>СВО</sub>	Collector cut-off current	$V_{CB} = 45 V$ $V_{CB} = 60 V$ $V_{CB} = 80 V$ $V_{CB} = 100 V$	$I_{E} = 0$ $I_{E} = 0$ $I_{E} = 0$ $I_{E} = 0$		BDX53 BDX53A BDX53B BDX53C			0.2 0.2 0.2 0.2	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = 5 V	I <sub>C</sub> = 0					2	mA
h <sub>FE</sub>	Forward current transfer ratio	V <sub>CE</sub> = 3 V	I <sub>C</sub> = 3 A	(see Notes 3 and 4	4)	750			
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>B</sub> = 12 mA	I <sub>C</sub> = 3 A	(see Notes 3 and 4	4)			2.5	۷
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>B</sub> = 12 mA	I <sub>C</sub> = 3 A	(see Notes 3 and 4	4)			2	V
V <sub>EC</sub>	Parallel diode forward voltage	I <sub>E</sub> = 3 A	I <sub>B</sub> = 0					2.5	V

NOTES: 3. These parameters must be measured using pulse techniques,  $t_p$  = 300  $\mu s,$  duty cycle  $\leq 2\%.$ 

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R <sub>θJC</sub>	Junction to case thermal resistance			2.08	°C/W
$R_{\thetaJA}$	Junction to free air thermal resistance			62.5	°C/W

#### resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS <sup>†</sup>				ТҮР	MAX	UNIT
t <sub>on</sub>	Turn-on time	I <sub>C</sub> = 3 A	$I_{B(on)} = 12 \text{ mA}$	$I_{B(off)} = -12 \text{ mA}$		1		μs
t <sub>off</sub>	Turn-off time	$V_{BE(off)} = -4.5 V$	$R_L = 10 \ \Omega$	$t_p$ = 20 $\mu$ s, dc $\leq$ 2%		5		μs

<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

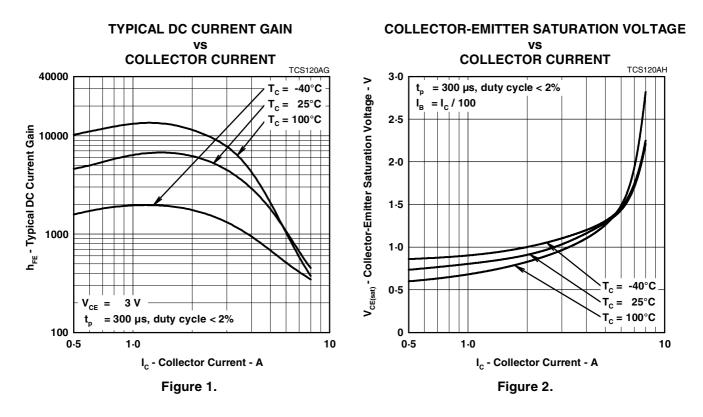


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### **TYPICAL CHARACTERISTICS**



**BASE-EMITTER SATURATION VOLTAGE** vs **COLLECTOR CURRENT** TCS120AI 3.0  $T_c = -40^{\circ}C$ V<sub>EE(sat)</sub> - Base-Emitter Saturation Voltage - V  $T_c = 25^{\circ}C$ Tc 100°C = 2.5 2.0 1.5 1.0 = I<sub>c</sub> / 100 I<sub>B</sub> = 300 µs, duty cycle < 2% 0.5 0.5 1.0 10 I<sub>c</sub> - Collector Current - A

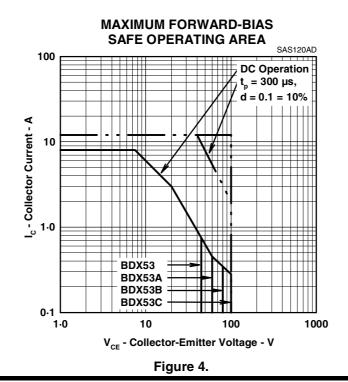


#### PRODUCT INFORMATION

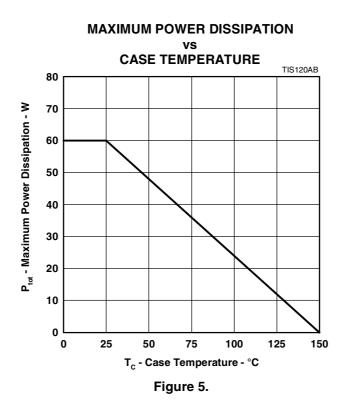
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# BDX53, BDX53A, BDX53B, BDX53C NPN SILICON POWER DARLINGTONS

#### MAXIMUM SAFE OPERATING REGIONS







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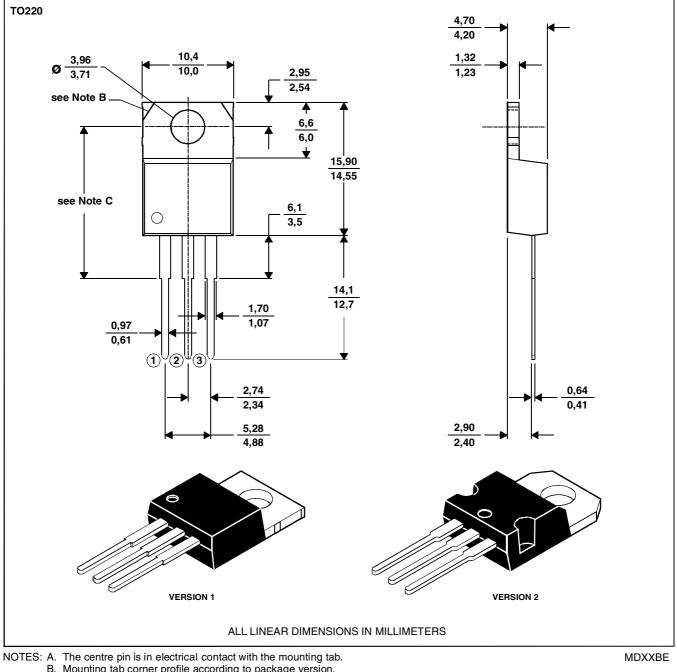
#### **MECHANICAL DATA**

### **TO-220**

### 3-pin plastic flange-mount package

BOURNS®

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

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